

*26*  
~~27~~ (new) A CVD apparatus as stated in claim 25, wherein the switch includes a first station for connecting the partitioning wall to the RF power supply for feeding a cleaning RF power and a second station for connecting the partitioning wall to a ground for cleaning using the RF power supplied to the radio-frequency electrode in the first chamber.

*27*  
~~28~~ (new) A CVD apparatus as stated in claim 17, further comprising an RF power supply for feeding a cleaning RF power and a switch for connecting the partitioning wall section to the RF power supply with suitable timing so as to produce a cleaning plasma in the film deposition process space.

*Rel. 126*  
*28*  
*A1*  
*cut*  
~~29~~ (new) A CVD apparatus as stated in claim 20, wherein the connecting means includes a switch which selectively connects the partitioning wall to the RF power supply for feeding a cleaning RF power and to a ground for cleaning using the RF power supplied to the radio-frequency electrode in the first chamber.

*229*  
~~30~~ (new) A CVD apparatus as stated in claim 28, wherein the switch includes a first station for connecting the partitioning wall to the RF power supply for feeding a cleaning RF power and a second station for connecting the partitioning wall to a ground for cleaning using the RF power supplied to the radio-frequency electrode in the first chamber.

*Revised*

*30*

31. (new) A CVD apparatus as stated in claim 1, further comprising a circuit for connecting the partitioning wall to ground while a cleaning power is applied to the radio-frequency electrode so as to produce a cleaning plasma in the film deposition process space.

*A1*  
*cut*

